

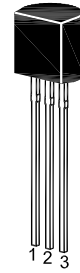
2SC535

NPN Silicon Epitaxial Planar Transistor

VHF amplifier, mixer, local oscillator.

The transistor is subdivided into two groups B and C according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



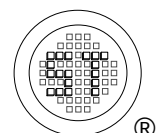
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

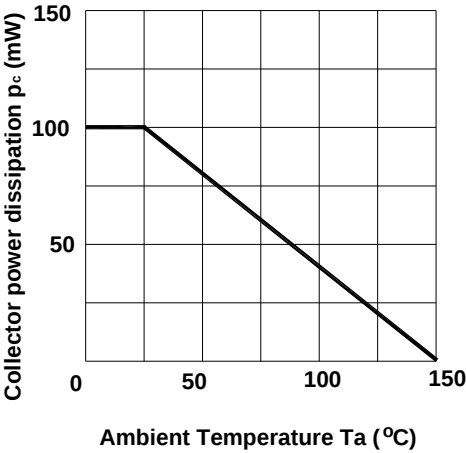
Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

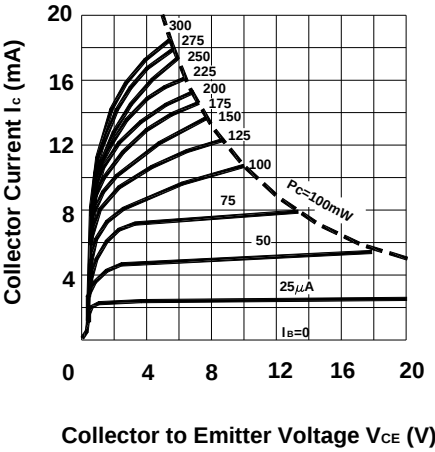
Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group B C	h_{FE}	60	-	120	-
	h_{FE}	100	-	200	-
Collector Base Cutoff Current at $V_{CB} = 10\text{ V}$	I_{CBO}	-	-	500	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 5\text{ mA}$	f_T	-	940	-	MHz
Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	-	1.2	pF



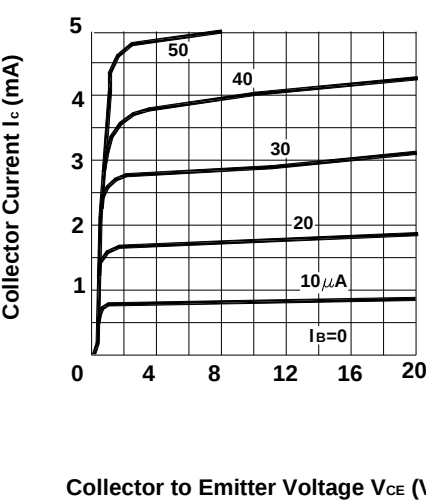
Maximum Collector Dissipation Curve



Typical Output Characteristics



Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current

